

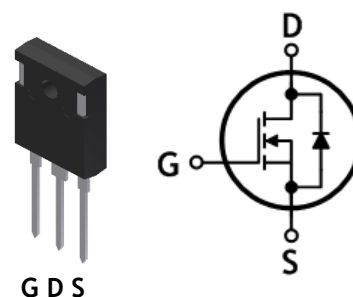
N-Channel Super Junction MOSFET

Features

- Drain-Source voltage: $V_{DS}=700V$ (@ $T_J=150^{\circ}C$)
- Low drain-source On resistance: $R_{DS(on)}=0.19\Omega$ (Max.)
- Ultra low gate charge: $Q_g=20nC$ (Typ.)
- RoHS compliant device
- 100% avalanche tested

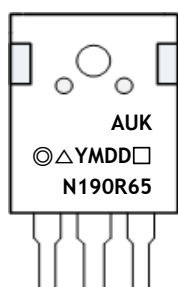
Ordering Information

Part Number	Marking	Package
SJMN190R65W	N190R65	TO-247



TO-247

Marking Information



Column 1: Manufacturer
Column 2: Production Information

e.g.) ◎△YMDD□

-. ◎: Management Code

-. △: Machine Code

-. YMDD: Data Code (Year, Month, Daily)

-. □: Factory Management Code

Column 3: Device Code

Absolute maximum ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Drain current (DC) (Note 1)	I_D	$T_C=25^{\circ}C$	20
		$T_C=100^{\circ}C$	12.6
Drain current (Pulsed) (Note 1)	I_{DM}	80	A
Single pulsed avalanche energy (Note 2)	E_{AS}	265	mJ
Repetitive avalanche current (Note 1)	I_{AR}	7	A
Repetitive avalanche energy (Note 1)	E_{AR}	15	mJ
Power dissipation	P_D	150	W
Diode dv/dt ruggedness (Note 3)	dv/dt	15	V/ns
MOSFET dv/dt ruggedness (Note 4)	dv/dt	50	V/ns
Junction temperature	T_J	150	$^{\circ}C$
Storage temperature range	T_{stg}	-55~150	$^{\circ}C$

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 0.83	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$, $V_{DS}=V_{GS}$	2	3	4	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=650\text{V}$, $T_J=125^{\circ}\text{C}$	-	-	100	μA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=10\text{A}$	-	0.155	0.19	Ω
Internal gate resistance	R_g	$f=1\text{MHz}$, Open drain	-	18	-	Ω
Input capacitance	C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	-	1533	-	pF
Output capacitance	C_{oss}		-	846	-	
Reverse transfer capacitance	C_{rss}		-	23	-	
Turn-on delay time (Note 5)	$t_{d(on)}$	$V_{DS}=350\text{V}$, $I_D=20\text{A}$, $R_G=25\Omega$	-	25	-	ns
Rise time (Note 5)	t_r		-	21	-	
Turn-off delay time (Note 5)	$t_{d(off)}$		-	60	-	
Fall time (Note 5)	t_f		-	4	-	
Total gate charge (Note 6)	Q_g	$V_{DS}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=10\text{A}$	-	36	-	nC
Gate-source charge (Note 6)	Q_{gs}		-	10	-	
Gate-drain charge (Note 6)	Q_{gd}		-	10	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	20	A
Source current (Pulsed)	I_{SM}		-	-	80	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=20\text{A}$	-	-	1.2	V
Reverse recovery time (Note 5, 6)	t_{rr}	$I_S=20\text{A}$, $V_{GS}=0\text{V}$, $dI_S/dt=100\text{A}/\mu\text{s}$	-	383	-	ns
Reverse recovery charge (Note 5, 6)	Q_{rr}		-	4.6	-	μC

Note:

1. Calculated continuous current based on maximum allowable junction temperature
2. $L=10\text{mH}$, $I_{AS}=7\text{A}$, $V_{DD}=50\text{V}$, Starting $T_J=25^{\circ}\text{C}$
3. $I_S \leq 20\text{A}$, $V_{DS} \leq 400\text{V}$, $dI_S/dt \leq 100\text{A}/\mu\text{s}$, $T_J=25^{\circ}\text{C}$
4. $V_{DS} \leq 400\text{V}$, $I_S \leq 20\text{A}$
5. Guaranteed by design, not subject to production testing
6. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

Typical Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

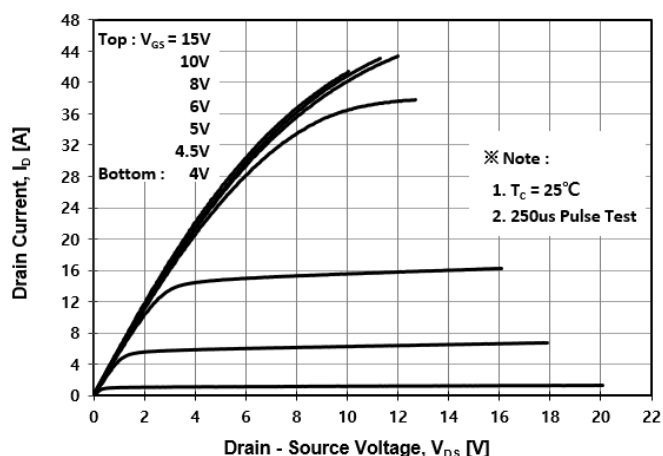


Fig. 2 Typical Transfer Characteristics

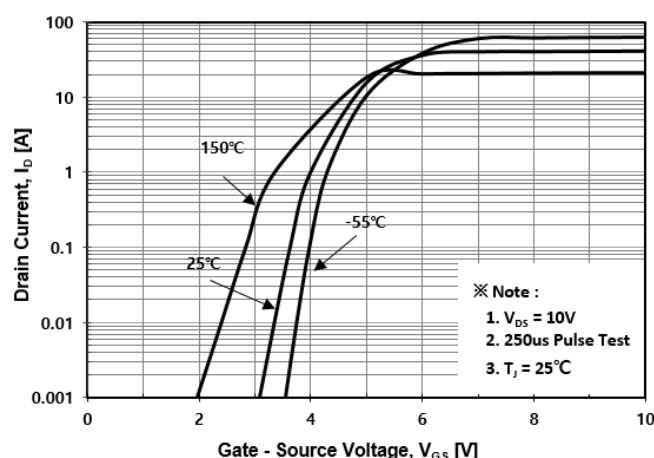


Fig. 3 On-Resistance Variation with Drain Current and Gate Voltage

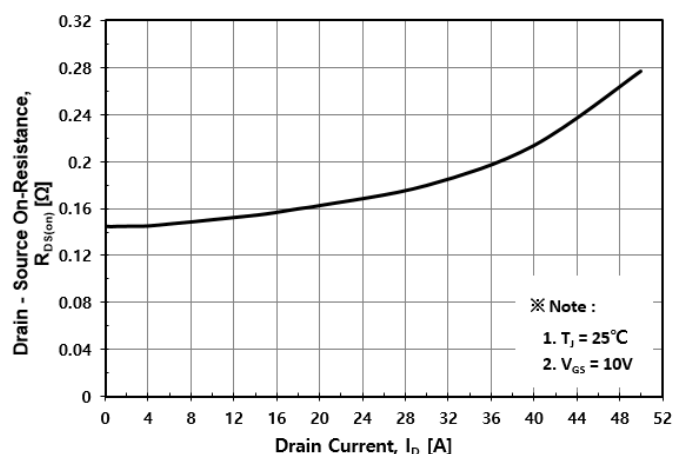


Fig. 4 Body Diode Forward Voltage Variation with Source Current

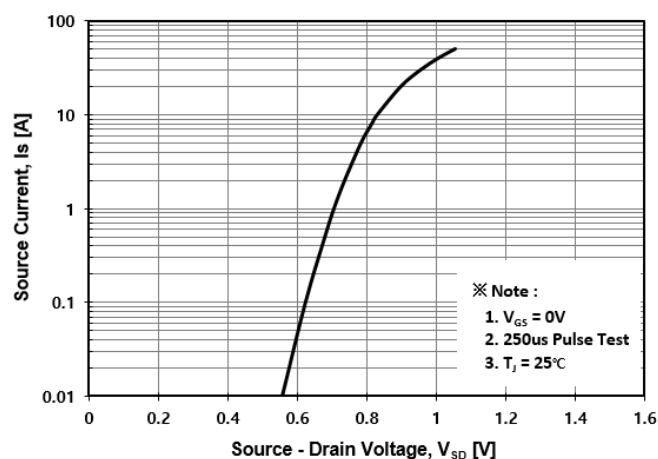


Fig. 5 Typical Capacitance Characteristics

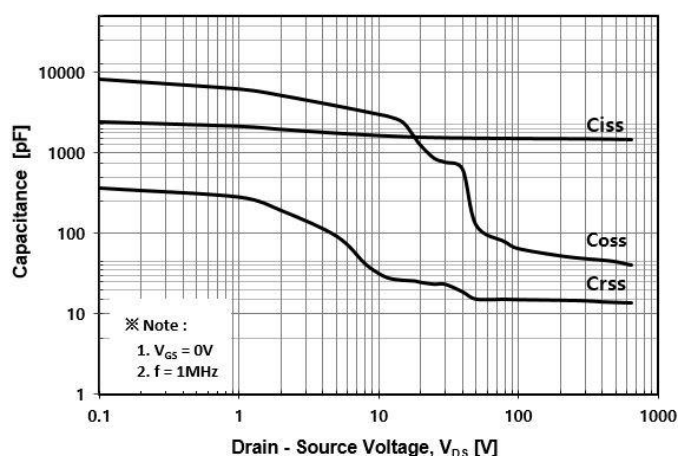
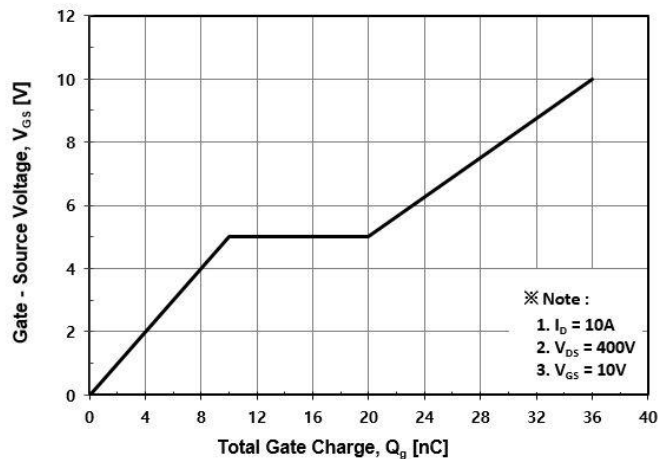


Fig. 6 Typical Total Gate Charge Characteristics



Typical Electrical Characteristics Curves

Fig. 7 Breakdown Voltage Variation vs. Temperature

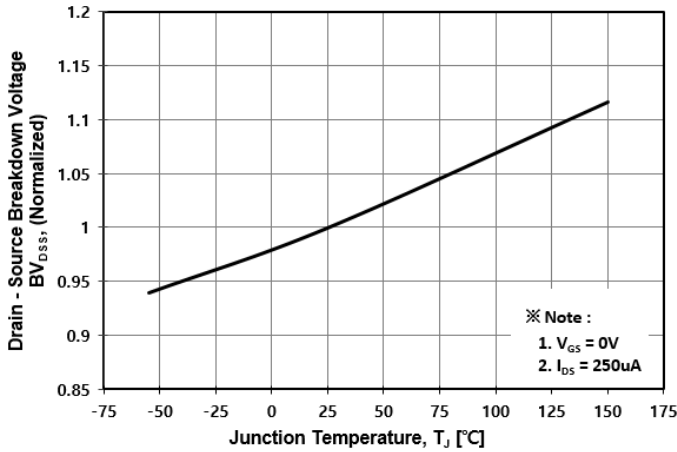


Fig. 8 On-Resistance Variation vs. Temperature

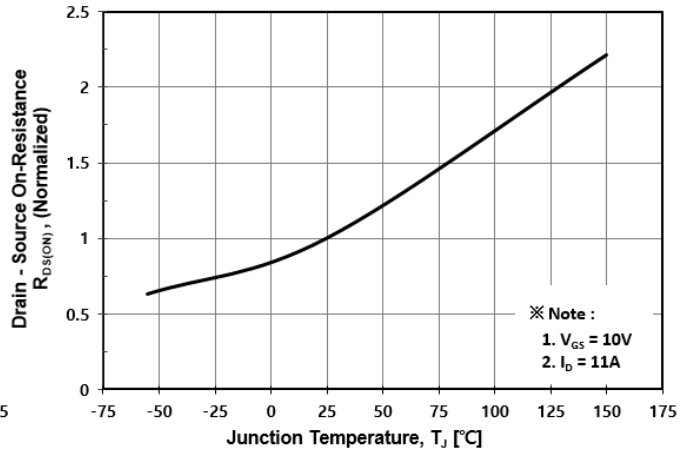


Fig. 9 Maximum Drain Current vs. Case Temperature

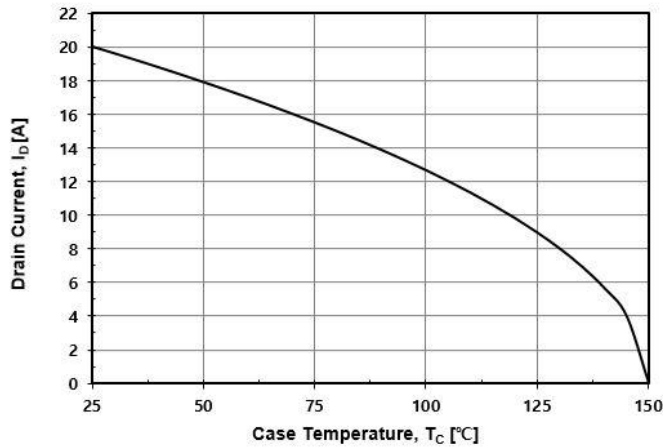


Fig. 10 Maximum Safe Operating Area

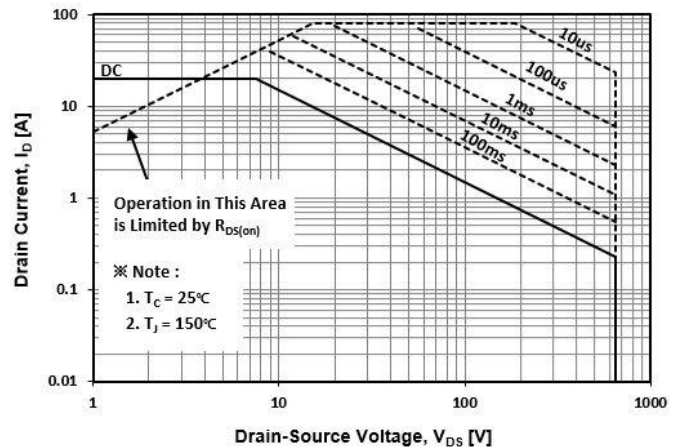


Fig. 11 Transient Thermal Impedance

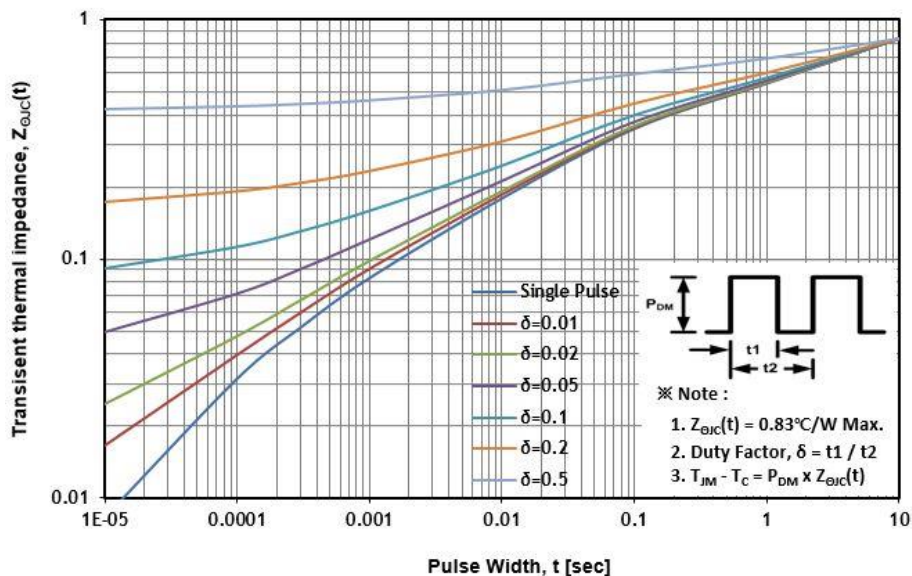


Fig. 12 Gate Charge Test Circuit & Waveform

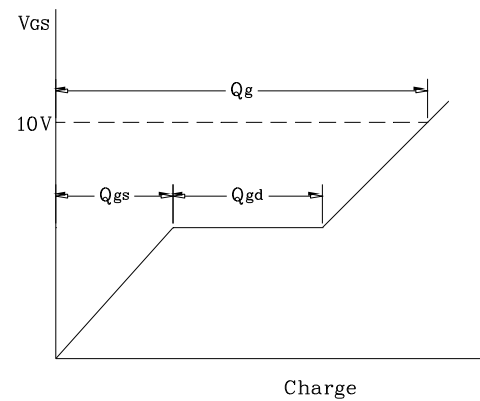
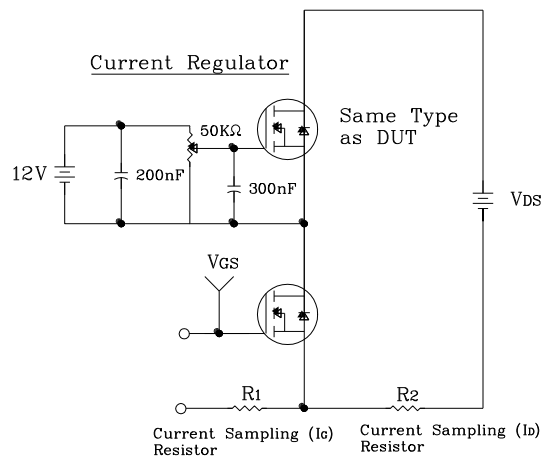


Fig. 13 Resistive Switching Test Circuit & Waveform

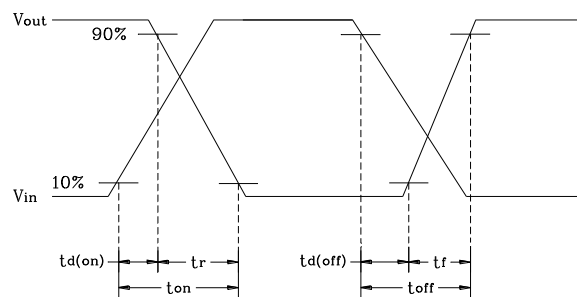
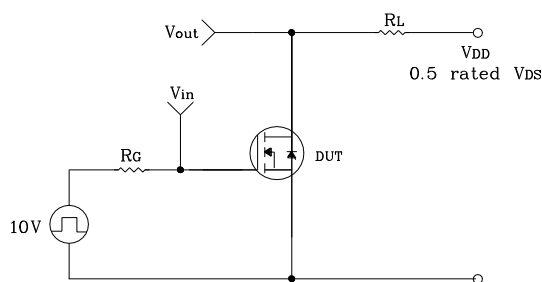


Fig. 14 EAS Test Circuit & Waveform

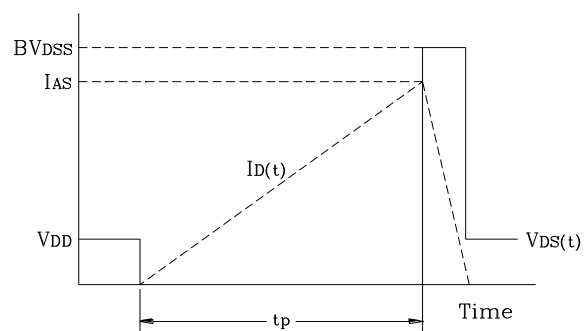
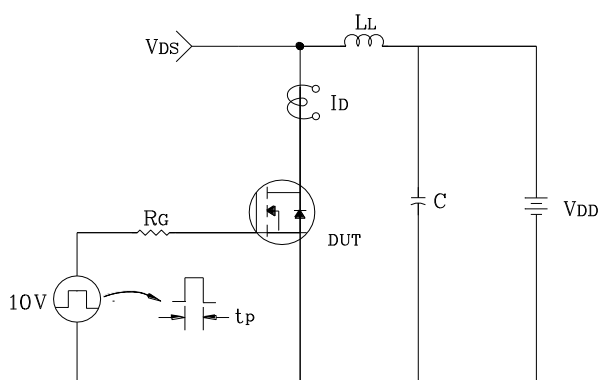
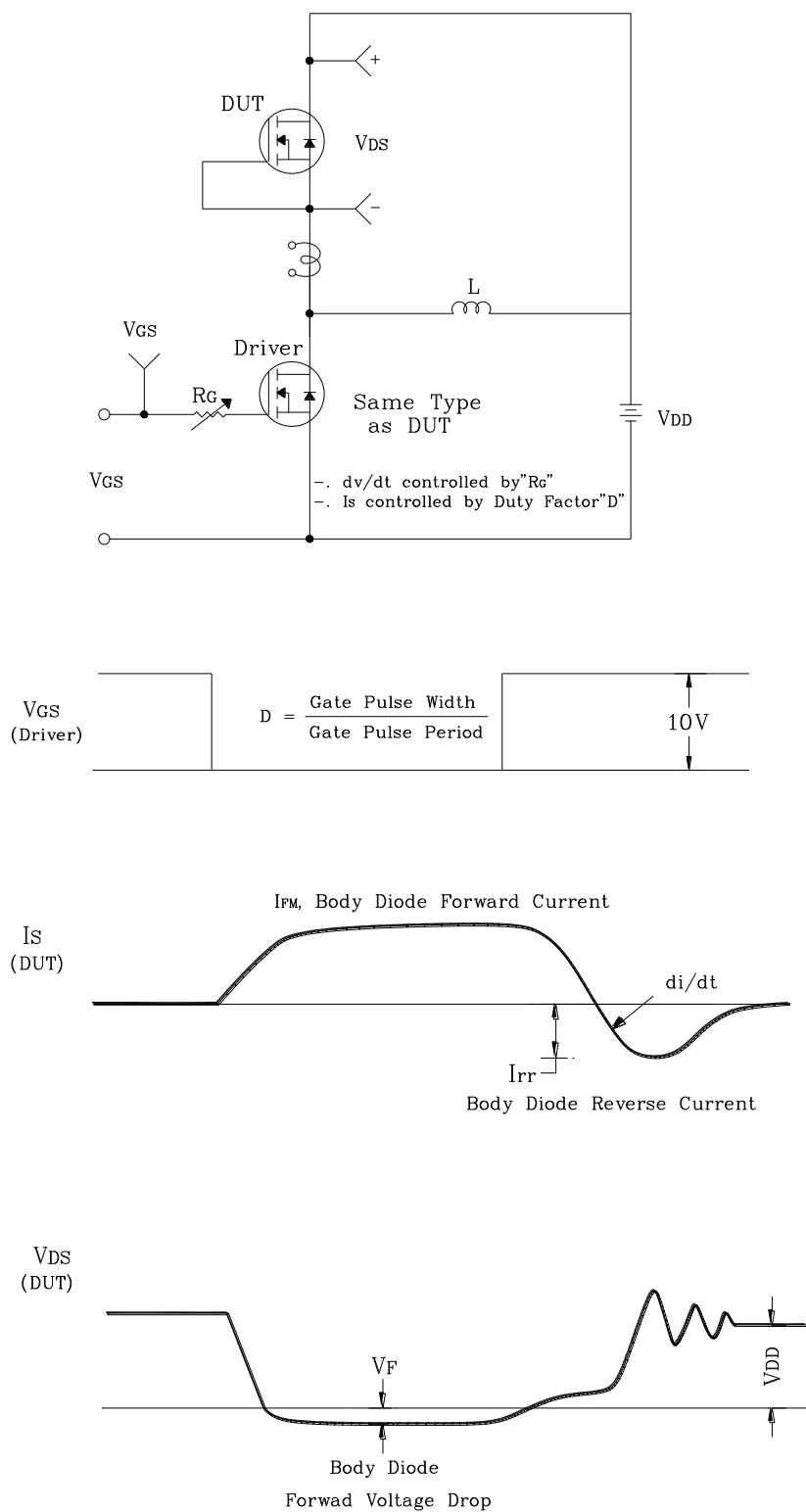
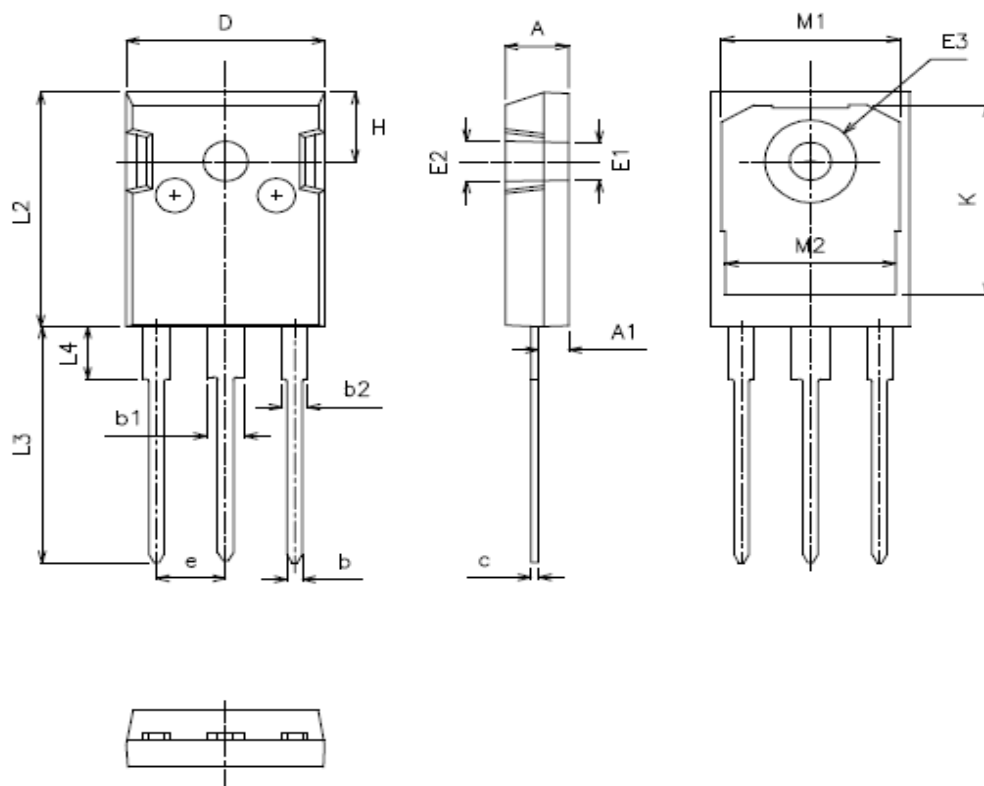


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.26	2.41	2.56
b	1.10	1.20	1.30
b1	3.00	3.10	3.20
b2	2.00	2.10	2.20
c	0.50	0.60	0.70
D	15.60	15.80	16.00
E1	3.45	3.60	3.75
E2	3.55	3.70	3.85
E3	7.04	7.19	7.34
L2	20.80	21.00	21.20
L3	19.72	19.92	20.12
L4	3.95	4.10	4.25
e	5.29	5.44	5.59
H	6.00	6.15	6.30
K	16.25	16.45	16.65
M1	13.80	14.00	14.20
M2	13.10	13.30	13.50

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